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PHASE CONTROL THYRISTOR AT980

Repetitive voltage up to **6000** V
Mean on-state current **3036** A
Surge current **50** kA

TARGET SPECIFICATION
set 08 - ISSUE : 05

Symbol	Characteristic	Conditions	Tj [℃]	Value	Unit
BLOCKING					
V_{RRM}	Repetitive peak reverse voltage		120	6000	V
V_{RSM}	Non-repetitive peak reverse voltage		120	6100	V
V_{DRM}	Repetitive peak off-state voltage		120	6000	V
I_{RRM}	Repetitive peak reverse current	V=VRRM	120	300	mA
I_{DRM}	Repetitive peak off-state current	V=VDRM	120	300	mA
CONDUCTING					
$I_{T(AV)}$	Mean on-state current	180° sin, 50 Hz, Th=55℃, dou ble side cooled		3036	A
$I_{T(AV)}$	Mean on-state current	180° sin, 50 Hz, Tc=85℃, dou ble side cooled		2244	A
I_{TSM}	Surge on-state current	sine wave, 10 ms	120	50,0	kA
I^2t	I^2t	without reverse voltage		12500 x1E3	A^2s
V_T	On-state voltage	On-state current = 6280 A	120	2,78	V
$V_{T(TO)}$	Threshold voltage		120	1,30	V
r_T	On-state slope resistance		120	0,235	mohm
SWITCHING					
di/dt	Critical rate of rise of on-state current, min.	From 75% VDRM , gate 10V, 5ohm	120	200	A/µs
dv/dt	Critical rate of rise of off-state voltage, min.	Linear ramp up to 70% of VDRM	120	1000	V/µs
td	Gate controlled delay time, typical	VD=100V, gate source 10V, 10 ohm , tr=.5 µs	25		µs
tq	Circuit commutated turn-off time, typical	dV/dt = 20 V/µs linear up to 75% VDRM		600	µs
Q rr	Reverse recovery charge	di/dt=-20 A/µs, I= 2150 A	120		µC
I rr	Peak reverse recovery current	VR= 50 V			A
I_H	Holding current, typical	VD=5V, gate open circuit	25	500	mA
I_L	Latching current, typical	VD=12V, tp=30µs	25	1000	mA
GATE					
V_{GT}	Gate trigger voltage	VD=12V	25	3,5	V
I_{GT}	Gate trigger current	VD=12V	25	400	mA
V_{GD}	Non-trigger gate voltage, min.	VD=VDRM	120	0,25	V
V_{FGM}	Peak gate voltage (forward)			10	V
I_{FGM}	Peak gate current			10	A
V_{RGM}	Peak gate voltage (reverse)			10	V
P_{GM}	Peak gate power dissipation	Pulse width 100 µs		150	W
P_G	Average gate power dissipation			3	W
MOUNTING					
$R_{th(j-h)}$	Thermal impedance, DC	Junction to heatsink, double side cooled		7,0	℃/kW
$R_{th(c-h)}$	Thermal impedance	Case to heatsink, double side cooled		1,0	℃/kW
T_j	Operating junction temperature			-30 / 120	℃
F	Mounting force			80 / 100	kN
	Mass			3000	g

ORDERING INFORMATION : AT980 S 60
standard specification — VDRM&VRRM/100

AT980 PHASE CONTROL THYRISTOR

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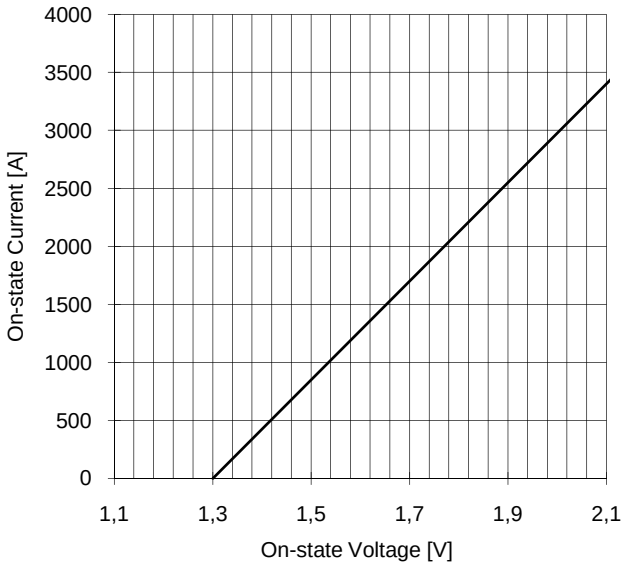
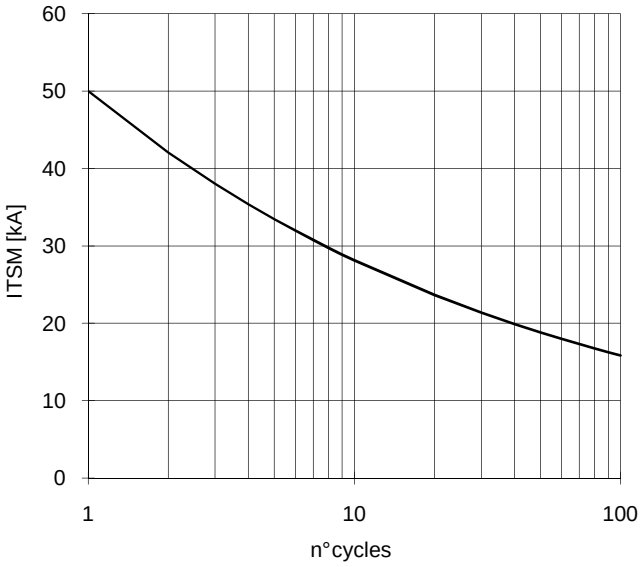
TARGET SPECIFICATION set 08 - ISSUE : 05

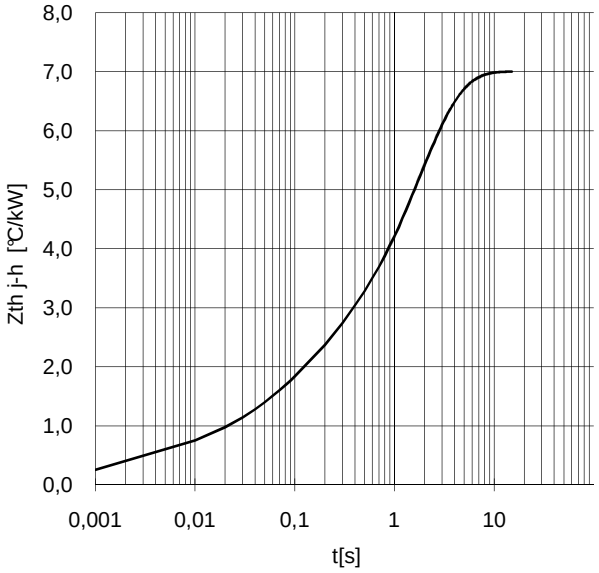
ON-STATE CHARACTERISTIC
Tj = 120 ℃

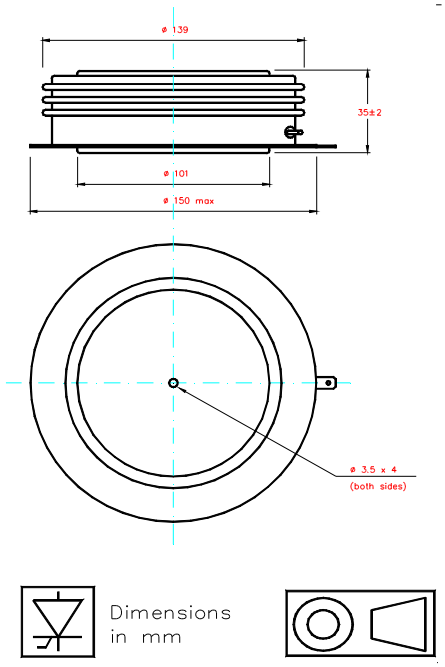


SURGE CHARACTERISTIC
Tj = 120 ℃



TRANSIENT THERMAL IMPEDANCE
DOUBLE SIDE COOLED





Cathode terminal type DIN 46244 - A 4.8 - 0.8

Gate terminal type AMP 60598 - 1

All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink, surfaces with flatness < .03 mm and roughness < 2 µm.
In the interest of product improvement POSEICO SpA reserves the right to change any data given in this data sheet at any time without previous notice.
If not stated otherwise the maximum value of ratings (simbols over shaded background) and characteristics is reported.

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